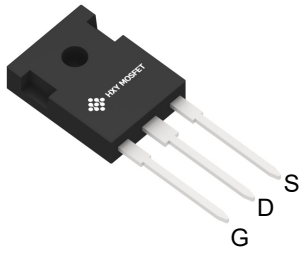
Description

The NTHL082N65S3F use super junction technology and design to provide excellent RDS(ON) with low gate charge. This super junction MOSFET fits the industry's AC-DC SMPS requirements for PFC, AC/DC power conversion, and industrial power applications.

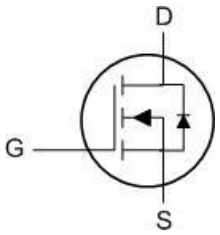
The NTHL082N65S3F meet the RoHS and Green Product requirement, 100% EAS guaranteed with full function reliability approved.



TO-247

Features

- Super Low Gate Charge
- 100% EAS Guaranteed
- Green Device Available
- Excellent CdV/dt effect decline
- Advanced trench gate super junction technology



Ordering Part Number	Package	Qty(PCS)
NTHL082N65S3F	TO-247	30

Maximum Ratings (T_C = 25 °C unless otherwise specifed)

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	650	V
V_{GS}	Gate-Source Voltage	±30	V
I_D@T_C=25˚C	Continuous Drain Current, V_{GS} @ 10V[1,6]	40	A
I_D@T_C=100˚C	Continuous Drain Current, V_{GS} @ 10V[1,6]	29	A
I_{DM}	Pulsed Drain Current[2]	160	A
EAS	Single Pulse Avalanche Energy[3]	750	mJ
I_{AS}	Avalanche Current	---	A
P_D@T_C=25˚C	Total Power Dissipation[4]	470	W
T_{STG}	Storage Temperature Range	-55 to 150	˚C
T_J	Operating Junction Temperature Range	-55 to 150	˚C
$R_{\theta JA}$	Thermal Resistance Junction-ambient[1]	41	˚C/W
$R_{\theta JC}$	Thermal Resistance Junction-Case[1]	0.27	˚C/W

Electrical Characteristics (at Tj = 25 °C, unless otherwise specified)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV_{DSS}	Drain-Source Breakdown Voltage	V_{GS}=0V , I_D=250uA	650	---	---	V
$\triangle BV_{DSS}/\triangle T_J$	BV_{DSS} Temperature Coefficient	Reference to 25℃ , I_D=1mA	---	---	---	V/℃
$R_{DS(ON)}$	Static Drain-Source On-Resistance[2]	V_{GS}=10V , I_D=21.5A	---	75	90	mΩ
		V_{GS}=4.5V , I_D=21.5A	---	---	---	
$V_{GS(th)}$	Gate Threshold Voltage	V_{GS}=V_{DS} , I_D =250uA	3.2	---	4.5	V
$\triangle V_{GS(th)}$	$_{GS(th)}$ Temperature Coefficient		---	---	---	mV/℃
I_{DSS}	Drain-Source Leakage Current	V_{DS}=650V , V_{GS}=0V , T_J=25℃	---	---	5	uA
		V_{DS}=650V, V_{GS}=0V , T_J=150℃	---	1000	---	
I_{GSS}	Gate-Source Leakage Current	V_{GS}=±30V , V_{DS}=0V	---	---	±100	nA
gfs	Forward Transconductance	V_{DS}=20V , I_D=21.5A	---	30	---	S
R_g	Gate Resistance	V_{DS}=0V , V_{GS}=0V , f=1MHz	---	1	---	Ω
Q_g	Total Gate Charge	V_{DS}=480V , V_{GS}=10V , I_D=21.5A	---	84	---	nC
Q_{gs}	Gate-Source Charge		---	28	---	
Q_{gd}	Gate-Drain Charge		---	36	---	
$T_{d(on)}$	Turn-On Delay Time	VGS=10V, VDS=400V, RG=27Ω, ID=21.5A	---	89	---	ns
T_r	Rise Time		---	131	---	
$T_{d(off)}$	Turn-Off Delay Time		---	204	---	
T_f	Fall Time		---	69	---	
C_{iss}	Input Capacitance	V_{DS}=100V , V_{GS}=0V , f=1MHz	---	3445	---	pF
C_{oss}	Output Capacitance		---	134	---	
C_{rss}	Reverse Transfer Capacitance		---	0.6	---	

Diode Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I_S	Continuous Source Current[1,4]	V_G=V_D=0V , Force Current	---	---	40	A
V_{SD}	Diode Forward Voltage[2]	V_{GS}=0V , I_S=21.5A , T_J=25°C	0.7	0.9	1.1	V
t_{rr}	Reverse Recovery Time	IF=21.5 , di/dt=100A/μs , T_J=25°C	---	113	---	nS
Q_{rr}	Reverse Recovery Charge		---	0.6	---	nC

Note :

1.The data tested by surface mounted on a 1 inch² FR-4 board with 2OZ copper.

2.The data tested by pulsed , pulse width ≦ 300us , duty cycle ≦ 2%

3.The EAS data shows Max. rating . The test condition is TJ = 25ÁC,VDD=200V,VGS=10V,L=30mH

4.The power dissipation is limited by 150℃ junction temperature

5.The data is theoretically the same as I_D and I_{DM} , in real applications , should be limited by total power dissipation.

Typical Performance Characteristics

Fig 1. Output Characteristics (T_j=25℃)

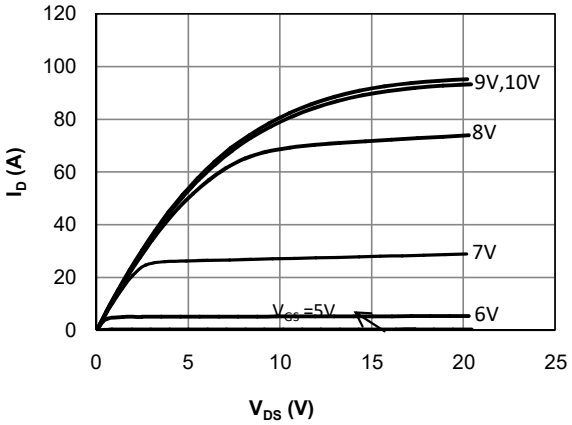


Fig 2. Output Characteristics (T_j=150℃)

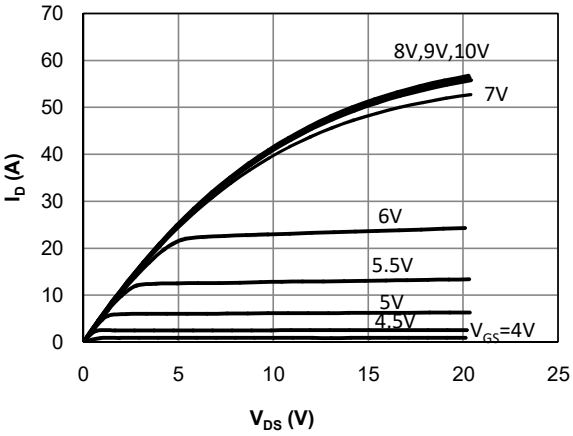


Fig 3: Transfer Characteristics

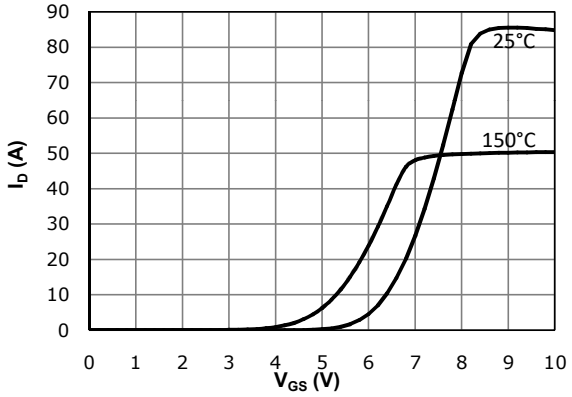


Fig 4: V_{TH} vs. T_j Temperature Characteristics

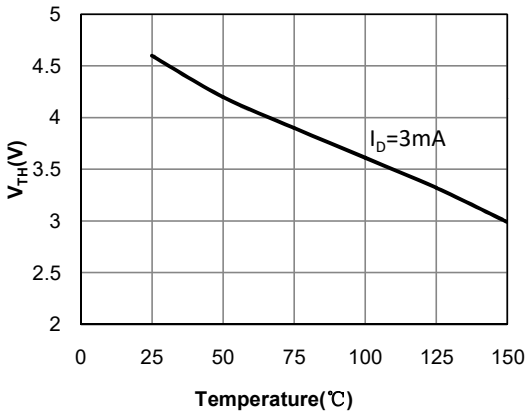


Fig 5: $R_{DS(on)}$ vs. I_{DS} Characteristics(T_j=25℃)

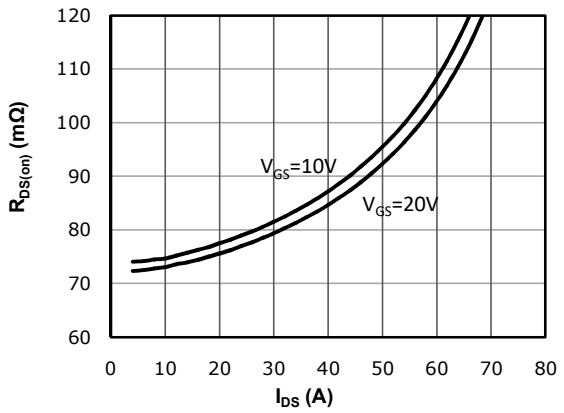


Fig 6: $R_{DS(on)}$ vs. Temperature

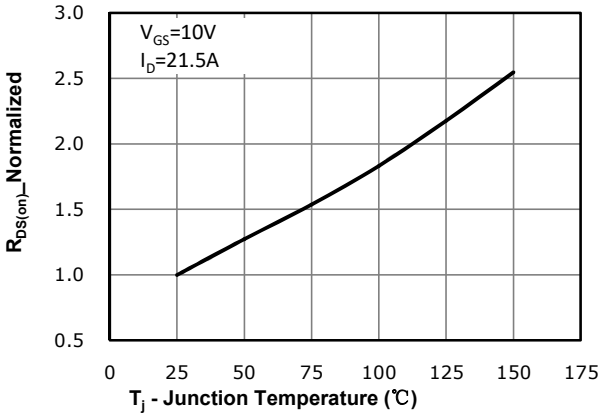


Fig 7: BV_{DSS} vs. Temperature

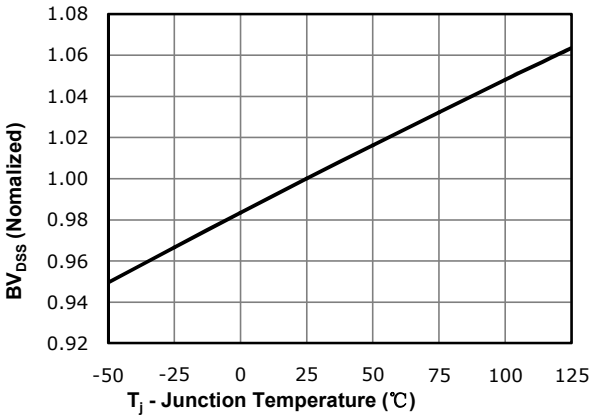


Fig 8: $R_{DS(on)}$ vs. Gate Voltage

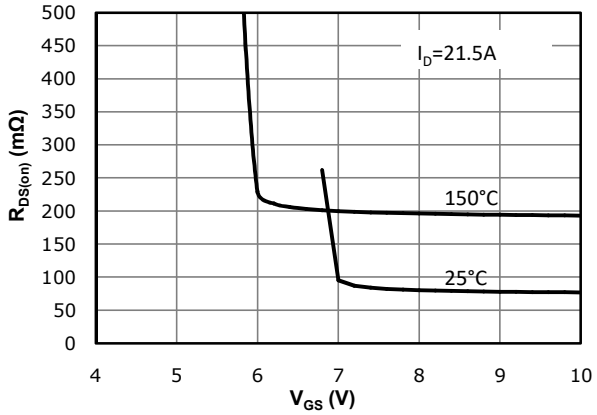


Fig 9: Body-diode Forward Characteristics

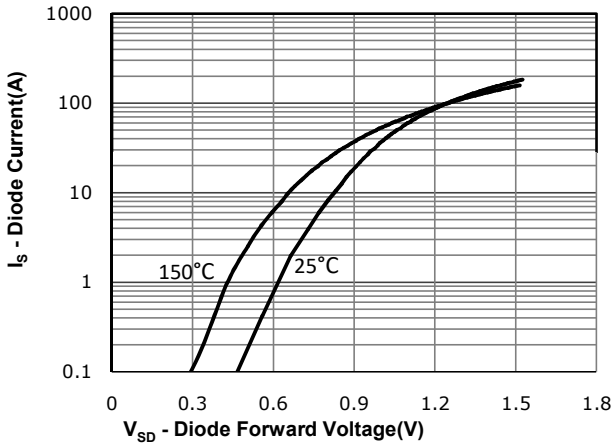


Fig 10: Gate Charge Characteristics

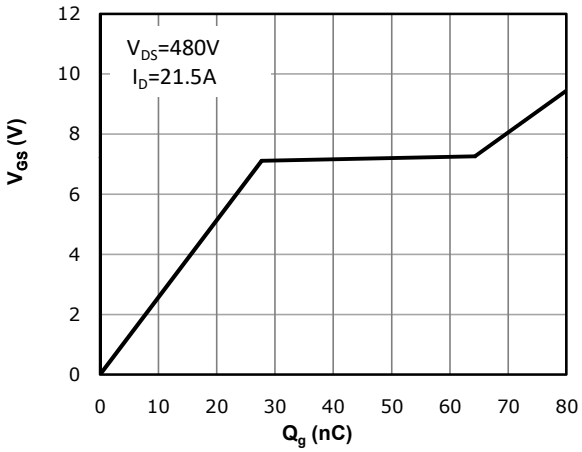


Fig 11: Capacitance Characteristics

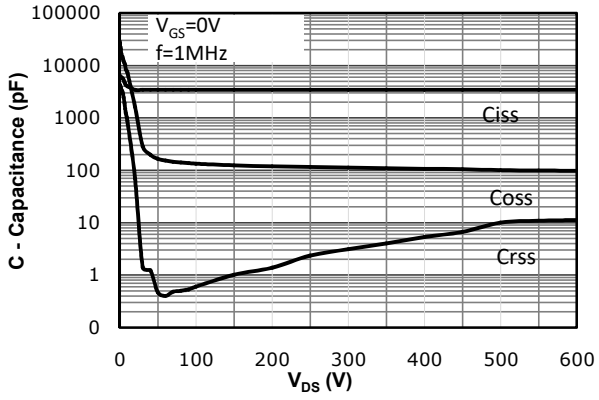


Fig 12: Safe Operating Area

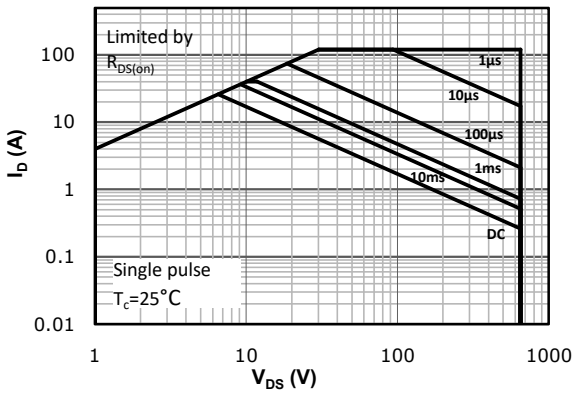
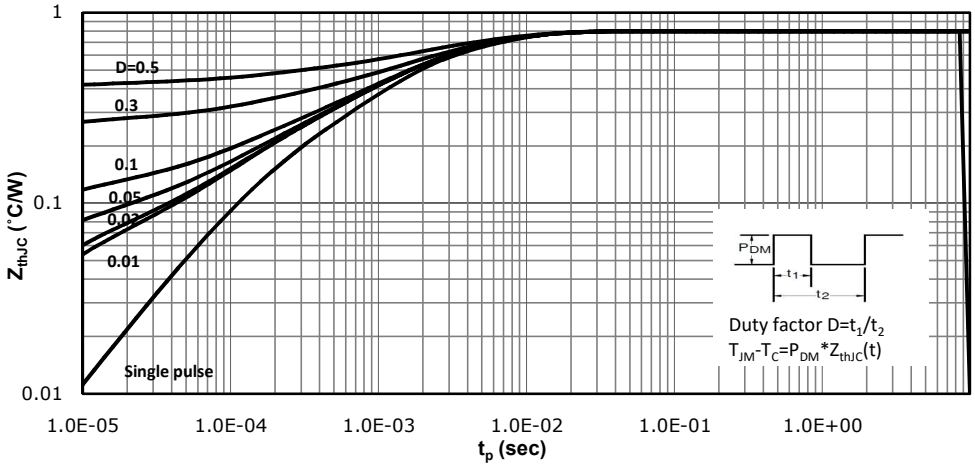
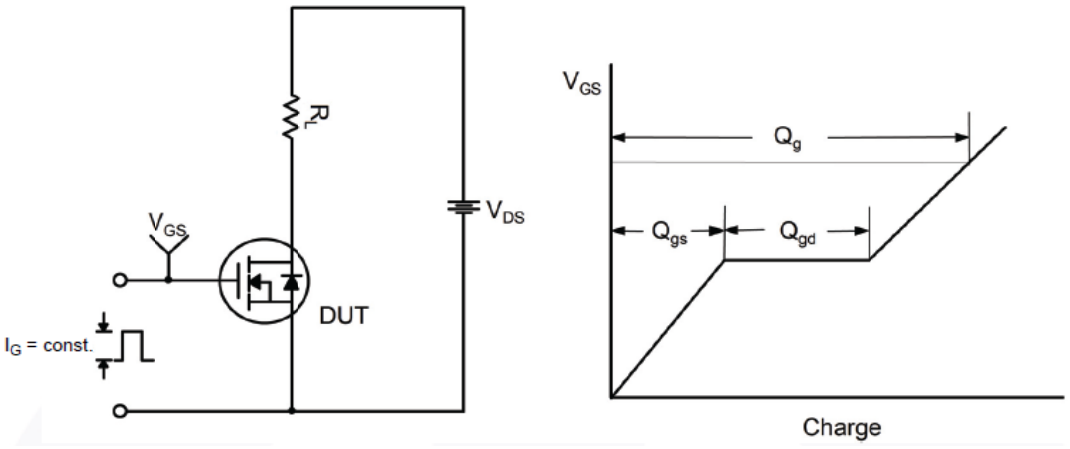


Fig 13: Max. Transient Thermal Impedance

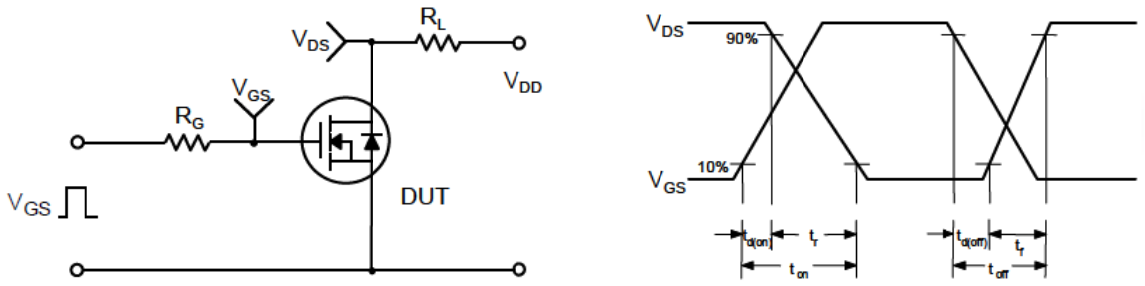


Test Circuit Schematic

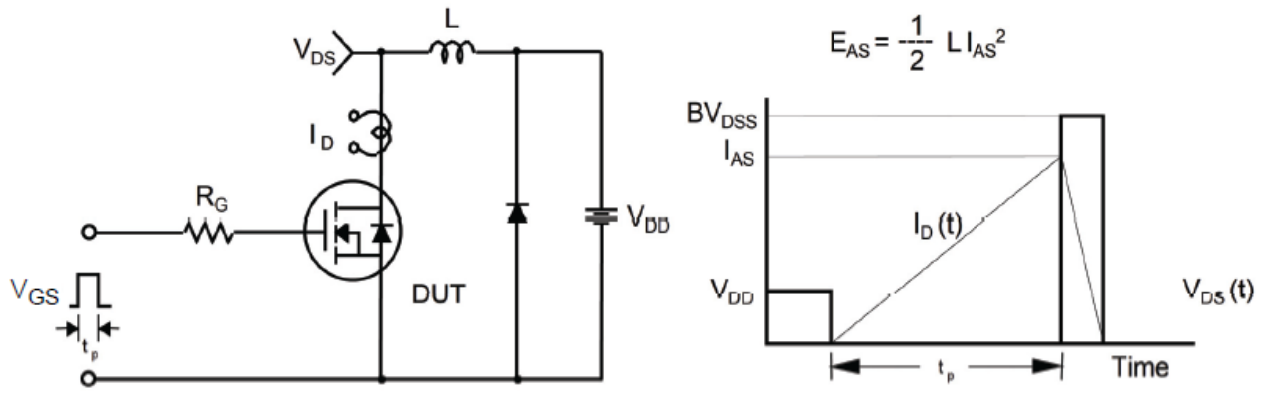
Gate Charge Test Circuit & Waveform



Switching Test Circuit & Waveforms

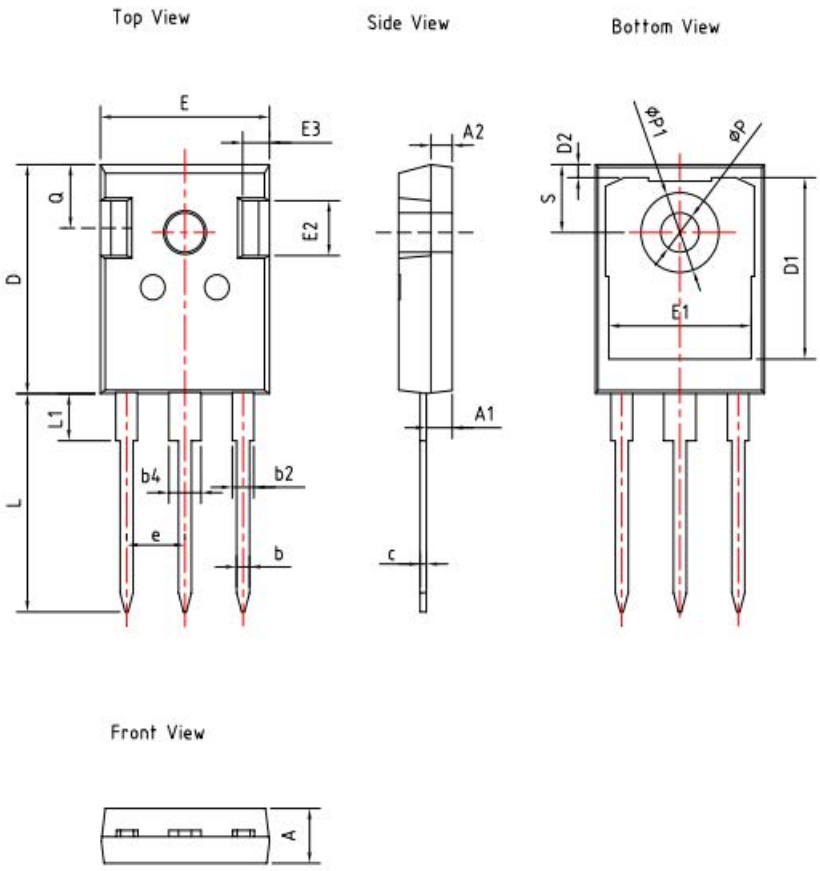


Unclamped Inductive Switching Test Circuit & Waveforms



Package Dimensions

Package TO-247



Dimension unit:[mm]			
SYMBOL	MIN	NOM	MAX
A	4.80	5.00	5.20
A1	2.21	2.41	2.61
A2	1.85	2.00	2.15
b	1.11	1.21	1.36
b2	1.91	2.01	2.21
b4	2.91	3.01	3.21
c	0.51	0.60	0.75
D	20.70	21.00	21.30
D1	16.25	16.55	16.85
D2	1.00	1.20	1.35
E	15.50	15.80	16.10
E1	13.00	13.30	13.60
E2	4.80	5.00	5.20
E3	2.30	2.50	2.70
e		5.44 BSC	
L	19.62	19.92	20.22
L1	-	-	4.30
ΦP	3.40	3.60	3.80
ΦP1	-	-	7.30
Q	5.40	5.80	6.20
S		6.20 BSC	

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